

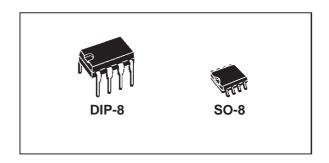
# **ST755**

# ADJUSTABLE INVERTING NEGATIVE OUTPUT CURRENT MODE PWM REGULATORS

- 2.7V TO 11V INPUT TO ADJUSTABLE NEGATIVE OUTPUT CONVERSION
- 1W GUARANTEED OUTPUT POWER (V<sub>in</sub>>4.5V, T≤70°C)
- 68% TYP. EFFICENCY AT 6V
- VERY LOW QUIESCENT CURRENT: 1.2mA IN ON MODE 10µA IN SHUT DOWN MODE
- SOFT START
- VERY LOW NOISE OUTPUT
- 160KHz FIXED FREQUENCY OSCILLATOR
- MIXED BIPOLAR-CMOS TECHNOLOGY

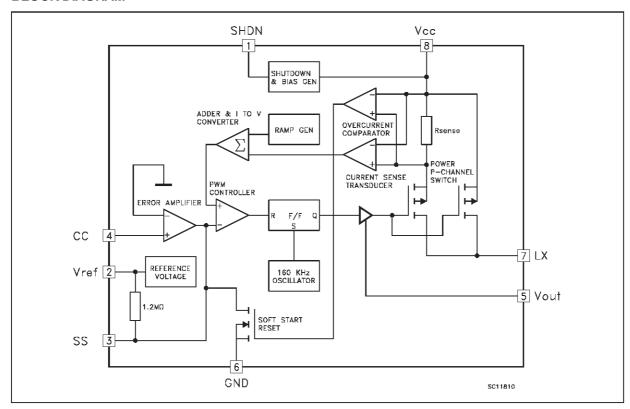


The ST755 is an adjustable inverting switch-mode DC-DC rergulator with internal Power MOSFET that generaters an adjustable negative output from a voltage input of 2.7V to 11V, output current guaranteed at 200mA (for



 $V_{in}>4.5V$ ,  $V_{out}=-5V$  and  $0^{o}C \leq Ta \leq 70^{o}C$ ) and 275mA (typical value at  $T_a=25$   $^{o}C$ ,  $V_{out}=-5V$ ). A logic controlled shut down pin that interfaces directly with microprocessor reduces supply current to only  $10\mu A$ . Input to Output differential voltage is limited to  $V_{in}+|V_{out}|<12.7V$ . No load supply current is 1.2mA.

#### **BLOCK DIAGRAM**



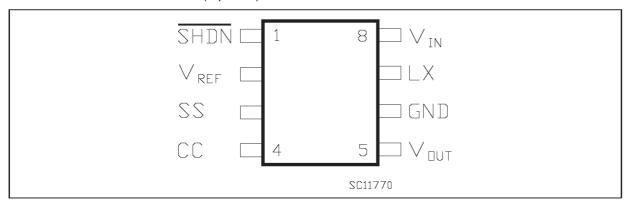
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#### **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
Vcc	DC Input Voltage to GND	-0.3 to 12	V
SHDN	Shutdown Voltage	-0.3 to V <sub>CC</sub> +0.3	V
	Other Input Voltage	-0.3 to V <sub>CC</sub> +0.3	V
I <sub>LX</sub>	Peak Switch Current	2	Α
P <sub>tot</sub>	Power Dissipation (at 70°C) (for <b>DIP-8</b> ) (for <b>SO-8</b> )	725 470	mW
Top	Operating Ambient Temperature Range	-40 to 85	°C
T <sub>stg</sub>	Storage Temperature Range	-55 to 150	°C

Absolute Maximum Rating are those values beyond which damage to the device may occur. Functional operation under these condition is not implied.

## **CONNECTION DIAGRAM AND (top view)**



#### **PIN CONNECTIONS**

Pin No	Symbol	Name and Function		
1	SHDN	SHUT-DOWN Control (Vcc = On, GND=Shutdown)		
2	$V_{ref}$	Reference Output Voltage (1.25V)		
3	SS	Soft Start		
4	CC	Compensation Input		
5	$V_{out}$	Negative Output Voltage		
6	GND	Ground		
7	LX	Switch Output		
8	Vcc	Positive Supply-Voltage Input		

#### **ORDERING NUMBERS**

Туре	DIP-8	SO-8 (Tube)	SO-8 (T&R)
ST755	ST755CN	ST755CD	ST755CD-TR

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**ELECTRICAL CHARACTERISTICS** (Refer to the test circuits,  $V_{CC} = 5V$ ,  $V_{out} = -5.25$  to -4.75V,  $I_{load} = 0$ mA,  $T_a = T_{min}$  to  $T_{max}$  unless otherwise specified. Typical Value are referred at  $T_a = 25$  °C)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
VIN	Input Voltage		2.7		11	V
Vo	Output Voltage	$I_0 = 0$ mA to 200 mA $V_{CC} = 4.5$ to 6.2 V	-5.25	-5	-4.75	V
I <sub>o</sub>	Output Current	$\begin{split} &V_{CC} = 4.5 \text{ to } 6.2  V  T_a = 0  ^{\circ}\text{C} \text{ to } 70  ^{\circ}\text{C} \\ &V_{CC} = 4.5 \text{ to } 6.2  V  T_a = -40  ^{\circ}\text{C} \text{ to } 85  ^{\circ}\text{C} \\ &V_{CC} = 4  V \qquad V_{out} = -5  V \\ &V_{CC} = 2.7  V \qquad V_{out} = -5  V \end{split}$	200 175	275 175 125		mA mA mA
I <sub>SUPPLY</sub>	Supply Current (Including Switching Current)	No Load, V <sub>SHDN</sub> = V <sub>CC</sub>		1.2	3.5	mA
$I_{OFF}$	Standby Current	No Load, V <sub>SHDN</sub> = 0V		10	100	μΑ
I <sub>SC</sub>	Short Circuit Current			1.2		А
$\Delta V_{\text{o}}$	Line Regulation	V <sub>CC</sub> = 4 to 6.2 V		0.1		%/V
$\Delta V_{\text{o}}$	Load Regulation	$I_0 = 0 \text{ mA to } 200 \text{ mA}$		0.003		%/mA
$V_{REF}$	Reference Voltage	$T_a = 25$ °C	1.18	1.25	1.32	V
$\Delta V_{REF}$	Reference Dritft	$T_a = T_{min}$ to $T_{max}$		50		ppm/°C
R <sub>DSON</sub>	LX On Resistance			0.7		Ω
I <sub>LEAK</sub>	LX Leakage Current	V <sub>DS</sub> = 10 V		1		μΑ
I <sub>SH</sub>	Shutdown Pin Current				1	μΑ
$V_{il}$	Shutdown Input Low Threshold				0.25	V
$V_{ih}$	Shutdown Input High Threshold		2			V
fo	Oscillator Frequency			160		KHz
ν	Power Efficency	$I_0 = 100 \text{ mA}$		68		%
CC	Compensation Pin Impedance			7.5		ΚΩ
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Do not overload or short the Output to Ground. If the above conditions are observerd, the device may be damaged.

#### **APPLICATION INFORMATION**

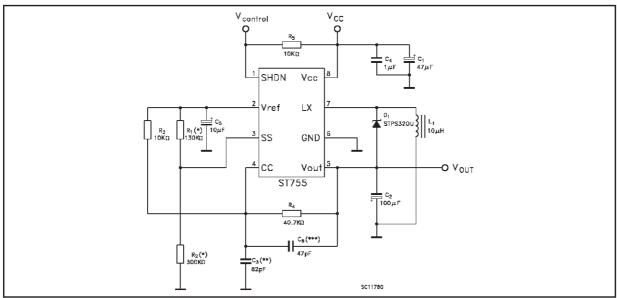
The ST755 is an IC developed for voltage conversion from an input voltage ranging from +2.4V to 11V to a regulated adjustable negative output limited by  $|V_{out}| \le 12.7V-V_{IN}$ . The circuit adopts a current-mode PWM control scheme to achieve good efficiency, high stability and low noise performance. The figure in the first page shown the detailed block diagram of the device. ST755 is realized in a BCD technology in order to achieve high temperature stability, the best REFERENCE precision, a very low quiescent current and jitter free operations. The final stage is built around a  $0.7\Omega$  - 2A P-Channel Power MOS. A fraction of the output current is splitted out for current detection. Internal clock frequency is fixed to 160KHz. Error amplifier drives the PWM comparator in order to keep 0V on the CC input. So R<sub>3</sub> and R<sub>4</sub> resistors are calculated by the following formulae  $R_4 = (|V_{out}|/V_{ref})^*R_3$  (see fig 1). For R<sub>3</sub> can be choosen any value between  $2K\Omega$  and  $20K\Omega$ . Soft-Start (SS) input is a voltage dependent-output current limit (see figure 9, Switch Current Limit vs. SS Input Voltage). SS pin is internally pulled to  $V_{ref}$  through a 1.2  $M\Omega$ resistor. Applying an appropiate capacitor at SS input is possible to obtain a soft-start current limitation during power up. Forcing Soft-Start (SS) input to a lower voltage through a resistive voltage driver (R1 and R2), the maximum LX curent limit can be lowered according the diagram showed in figure 9. When SHDN input is low, the total current consumption is reduced to 10μA.

#### **APPLICATION CIRCUIT**

To achieve the best performances from switching power supply topology, particular care to layout drawing is needed, in order to minimize EMI and obtain low noise, jitter free operation moreover, it ensures the full device functionality. Layout design proposed on demoboard (see picture 2) helps to lower the developing time.

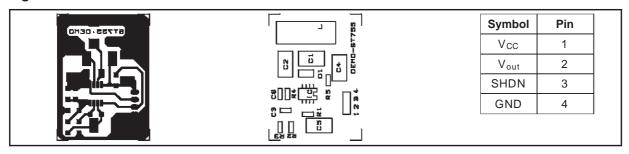
Wire lengths must be minimized, filter and by-pass capacitors C1, C2 and C3 must be low ESR type, placed as close possible to the integrated circuit. The 10µH inductor must be chosen built on a core, taking care that saturation current should be higher than the peak LX switch current. See the PEAK INDUCTOR CURRENT vs. LOAD CURRENT graph (figure 6)

Figure 1: TYPICAL APPLICATION CIRCUIT



- (\*) R1 and R2 can be omitted for lout<200mA.
- (\*\*) C6: Very low noise but poor transient and load response speed. (\*\*\*) C3 (alternative to C6): faster transient and load response.

Figure 2: Printed Demoboard



### Component Values

Capacitor	Value	Unit	Resistor	Value	Unit
C1	47	μF	R1	130	ΚΩ
C2	100	μF	R2	300	ΚΩ
C3	82	pF	R3	10	ΚΩ
C4	1	μF	R4	40.7	ΚΩ
C5	10	μF	R5	10	ΚΩ
C6	47	pF			

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#### TYPICAL OPERATING CHARACTERISTICS

Figure 3: Load Current vs Supply Voltage

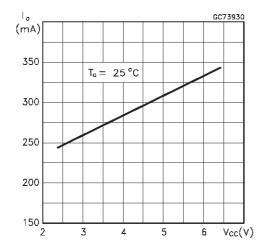
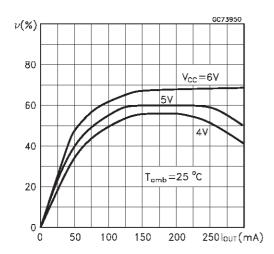


Figure 5: Efficency vs Load Current



**Figure 7:** Switch ON Resistance vs Supply Voltage

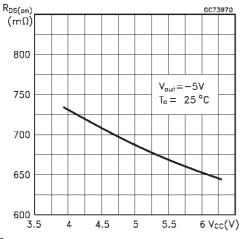


Figure 4: Load Current vs Supply Voltage

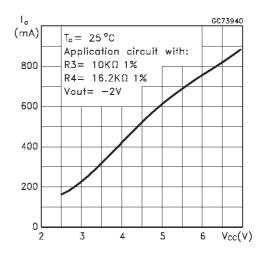
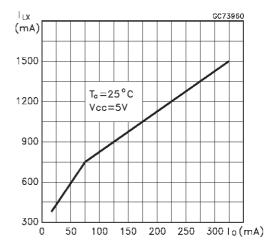
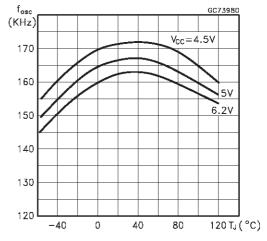


Figure 6: Peak InductorCurrent vs Load Current



**Figure 8:** Oscillator Frequency vs Temperature & Supply Voltage



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## TYPICAL OPERATING CHARACTERISTICS (continued)

**Figure 9:** Switch Current Limit vs Soft Start Voltage

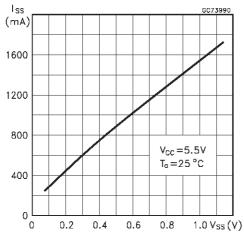


Figure 11: Soft Start Delay Time

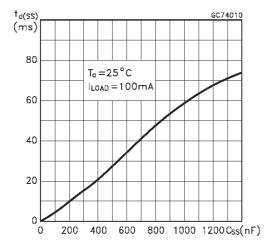
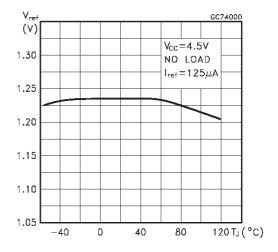


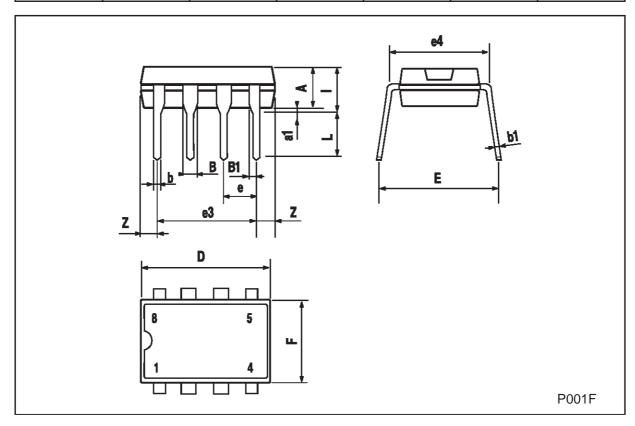
Figure 10: Reference Voltage vs temperature



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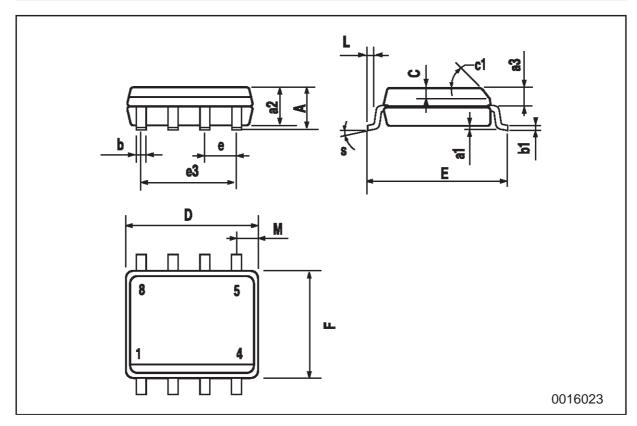
# Plastic DIP-8 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А		3.3			0.130	
a1	0.7			0.028		
В	1.39		1.65	0.055		0.065
B1	0.91		1.04	0.036		0.041
b		0.5			0.020	
b1	0.38		0.5	0.015		0.020
D			9.8			0.386
Е		8.8			0.346	
е		2.54			0.100	
e3		7.62			0.300	
e4		7.62			0.300	
F			7.1			0.280
I			4.8			0.189
L		3.3			0.130	
Z	0.44		1.6	0.017		0.063



# **SO-8 MECHANICAL DATA**

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А			1.75			0.068
a1	0.1		0.25	0.003		0.009
a2			1.65			0.064
a3	0.65		0.85	0.025		0.033
b	0.35		0.48	0.013		0.018
b1	0.19		0.25	0.007		0.010
С	0.25		0.5	0.010		0.019
c1			45	(typ.)		
D	4.8		5.0	0.188		0.196
Е	5.8		6.2	0.228		0.244
е		1.27			0.050	
e3		3.81			0.150	
F	3.8		4.0	0.14		0.157
L	0.4		1.27	0.015		0.050
М			0.6			0.023
S	8 (max.)					



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